## Description

The G2003A uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

## General Features

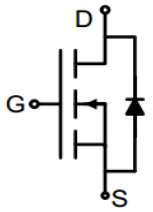
- $V_{DS}$ = 190V,$I_D$ =3A

  $R_{DS(ON)}$ < 540mΩ @ $V_{GS}$=10V (Typ:430mΩ)
  $R_{DS(ON)}$ < 560mΩ @ $V_{GS}$=10V (Typ:440mΩ)

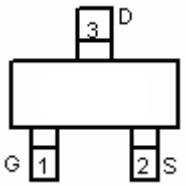
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation
- RoHS Compliant

## Application

- Power switching application




**Schematic Diagram**




**Marking and Pin Assignment**

**SOT-23-3L**

## Ordering Information

| Part Number | Marking | Case | Packaging |
|---|---|---|---|
| G2003A | G2003A | SOT-23-3L | 3000pcs/Reel |

## Absolute Maximum Ratings ($T_A$=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DS}$ | 190 | V |
| Gate-Source Voltage | $V_{GS}$ | ±20 | V |
| Drain Current-Continuous | $I_D$ | 3 | A |
| Drain Current-Pulsed (Note 1) | $I_{DM}$ | 8 | A |
| Maximum Power Dissipation | $P_D$ | 1.8 | W |
| Operating Junction and Storage Temperature Range | $T_J$,$T_{STG}$ | -55 To 150 | ℃ |

## Thermal Characteristic

| | | | |
|---|---|---|---|
| Thermal Resistance,Junction-to-Ambient (Note 2) | $R_{\theta JA}$ | 70 | ℃/W |

## Electrical Characteristics ($T_A$=25℃unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$=0V $I_D$=250μA | 190 | - | - | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$=190V,$V_{GS}$=0V | - | - | 1 | μA |

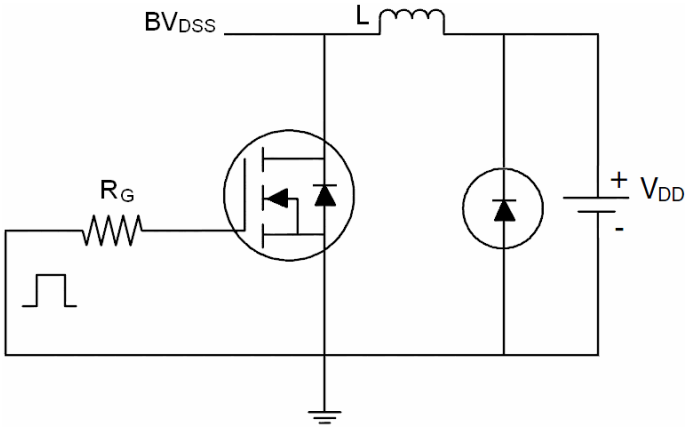
| | | | | | | |
|---|---|---|---|---|---|---|
| Gate-Body Leakage Current | $I_{GSS}$ | $V_{GS}$=±20V,$V_{DS}$=0V | - | - | ±100 | nA |
| **On Characteristics** (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$=$V_{GS}$,$I_D$=250μA | 1.0 | 1.7 | 3 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}$=10V, $I_D$=2A | - | 430 | 540 | mΩ |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}$=4.5V, $I_D$=2A | - | 440 | 560 | mΩ |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$=15V,$I_D$=2A | - | 8 | - | S |
| **Dynamic Characteristics** (Note4) | | | | | | |
| Input Capacitance | $C_{lss}$ | $V_{DS}$=25V,$V_{GS}$=0V, F=1.0MHz | - | 580 | - | PF |
| Output Capacitance | $C_{oss}$ | | - | 90 | - | PF |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 3 | - | PF |
| **Switching Characteristics** (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}$=100V, $R_L$=15Ω $V_{GS}$=10V,$R_G$=2.5Ω | - | 10 | - | nS |
| Turn-on Rise Time | $t_r$ | | - | 12 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 15 | - | nS |
| Turn-Off Fall Time | $t_f$ | | - | 15 | - | nS |
| Total Gate Charge | $Q_g$ | $V_{DS}$=100V,$I_D$=2A, $V_{GS}$=10V | - | 12 | | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 2.5 | - | nC |
| Gate-Drain Charge | $Q_{gd}$ | | - | 3.8 | - | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| Diode Forward Voltage (Note 3) | $V_{SD}$ | $V_{GS}$=0V,$I_S$=3A | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | $I_S$ | | - | - | 3 | A |

## Notes:

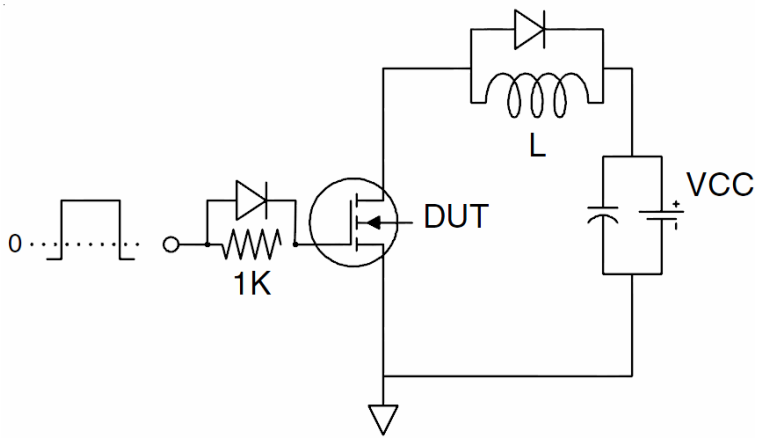
**1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
**2.** Surface Mounted on FR4 Board, t ≤ 10 sec.
**3.** Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
**4.** Guaranteed by design, not subject to production

## Test Circuit

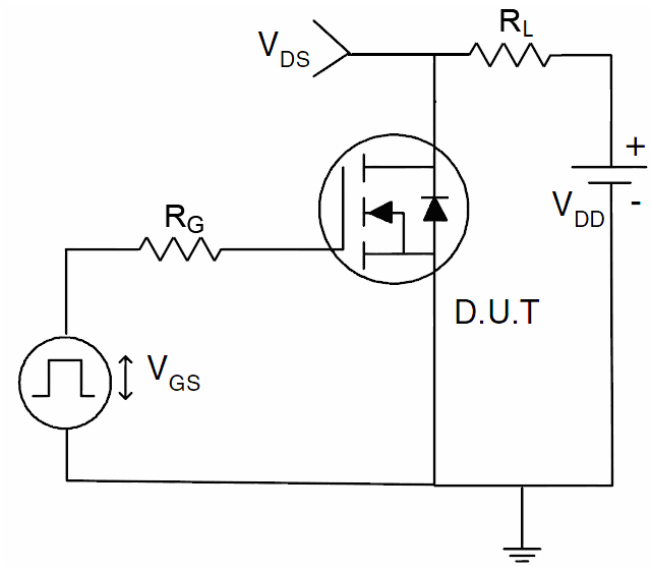
1）$E_{AS}$ test circuit




2）Gate charge test circuit




3）Switch Time Test Circuit



## Typical Electrical and Thermal Characteristics (Curves)

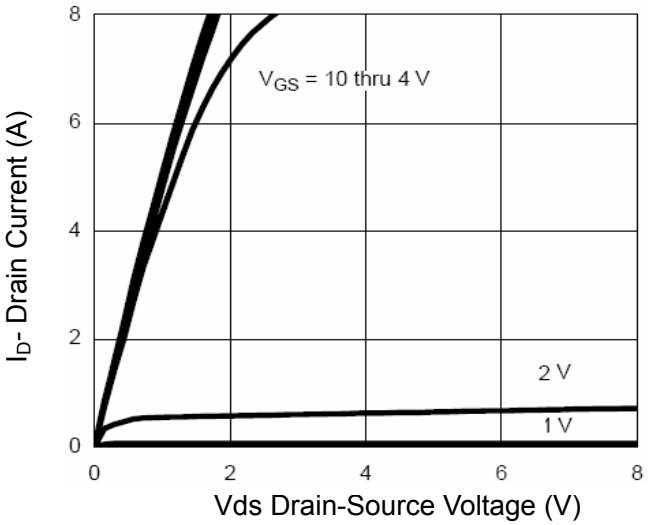



**Figure 1 Output Characteristics**

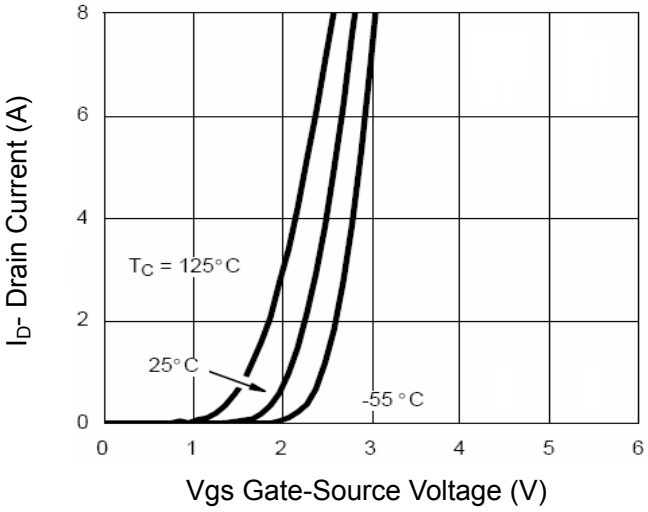



**Figure 2 Transfer Characteristics**

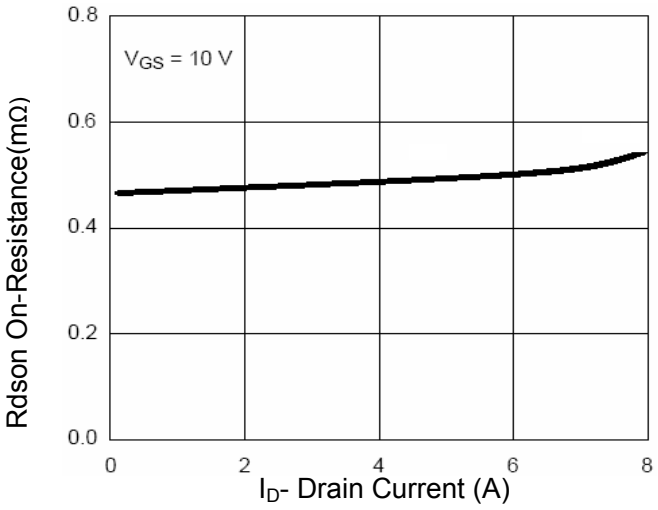



**Figure 3 Rdson- Drain Current**

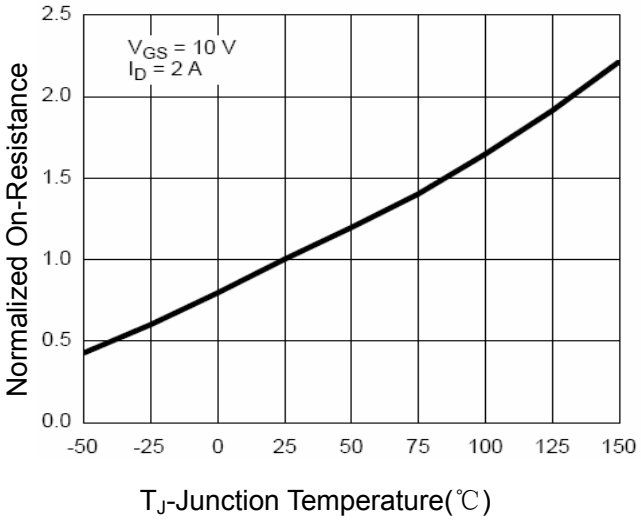



**Figure 4 Rdson-JunctionTemperature**

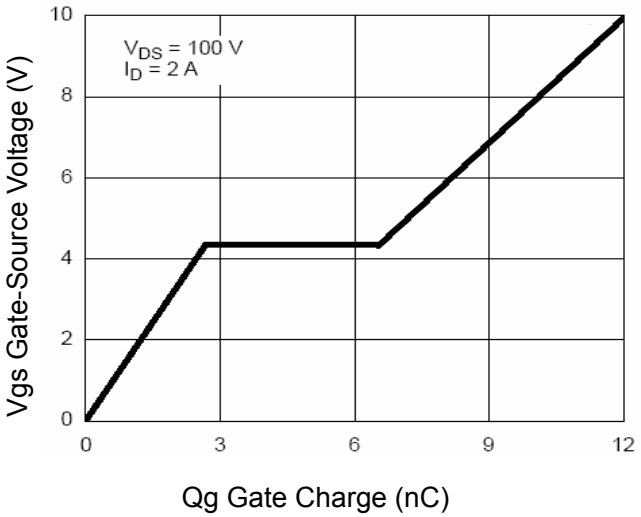



**Figure 5 Gate Charge**

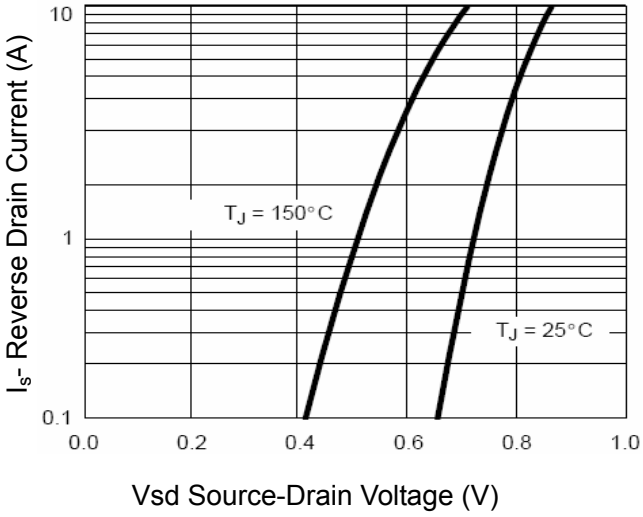



**Figure 6 Source- Drain Diode Forward**

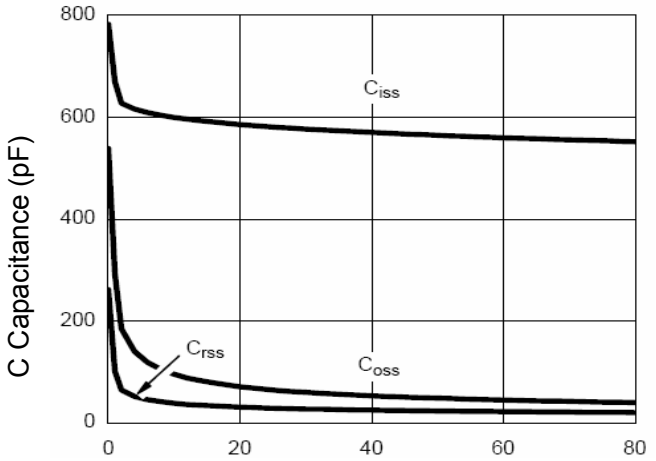



**Figure 7 Capacitance vs Vds**

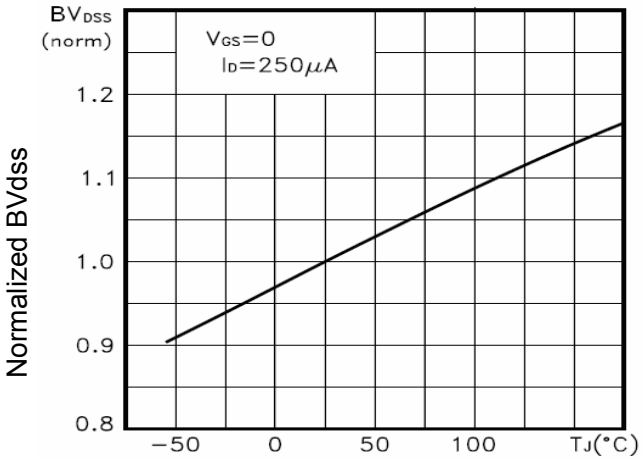



**Figure 9 $BV_{DSS}$ vs Junction Temperature**

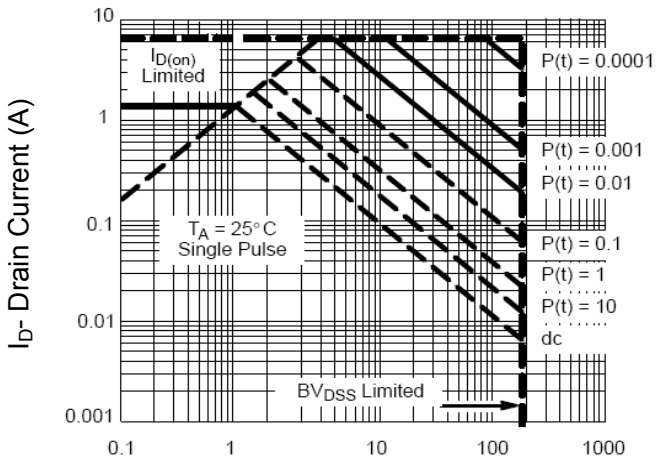



**Figure 8 Safe Operation Area**

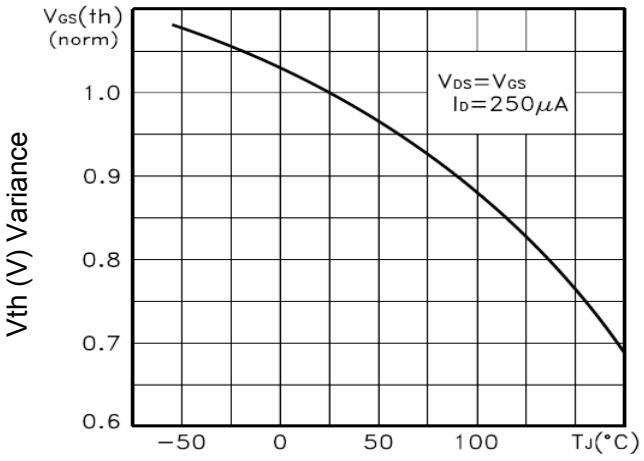



**Figure 10 $V_{GS(th)}$ vs Junction Temperature**

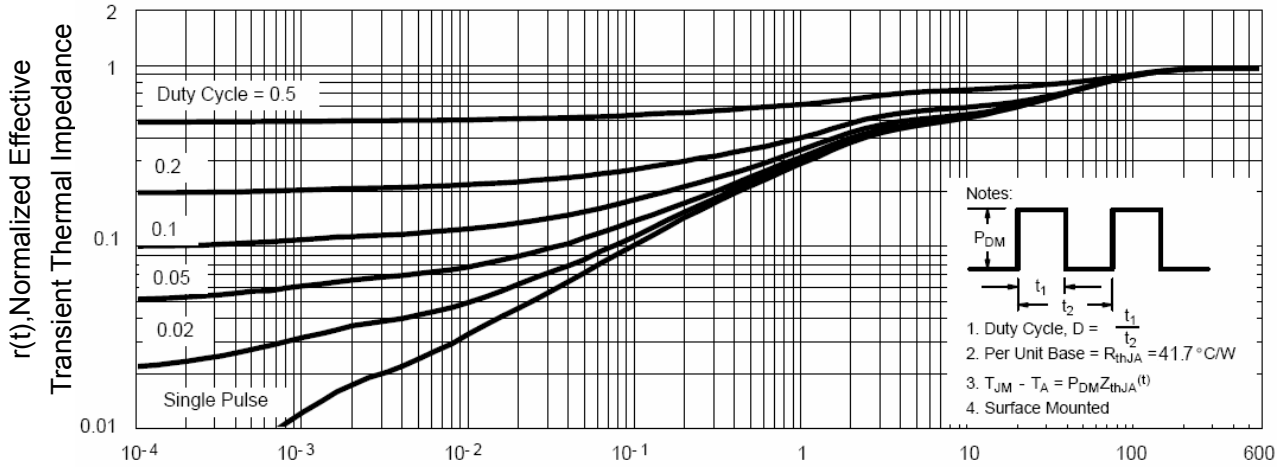
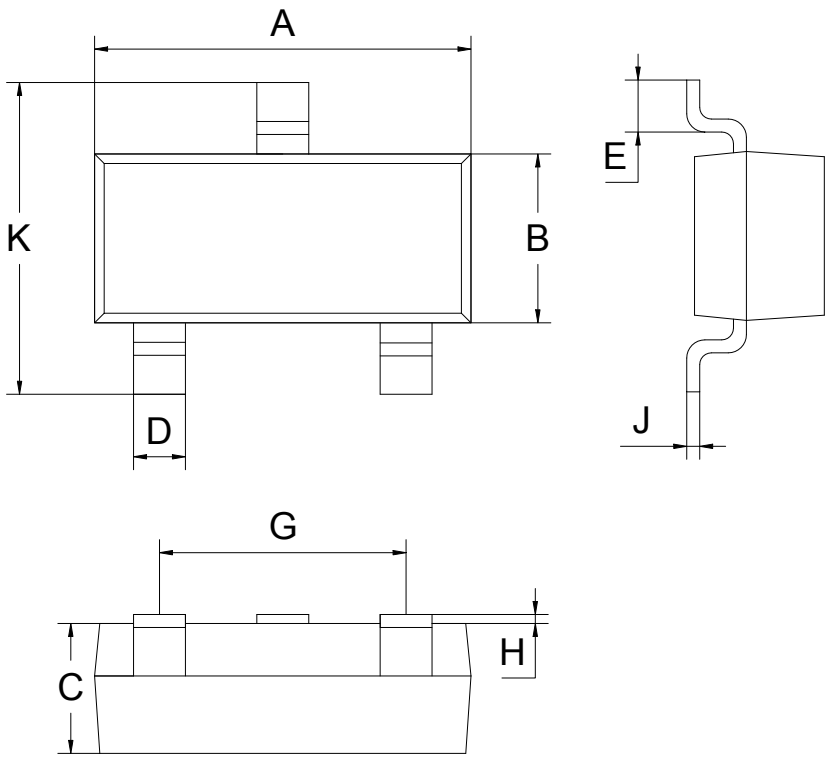



**Figure 11 Normalized Maximum Transient Thermal Impedance**

## SOT-23-3L package information




| SOT-23-3L | | | |
|---|---|---|---|
| Dim | MIN | NOM | MAX |
| A | 2.80 | 2.90 | 3.00 |
| B | 1.50 | 1.60 | 1.70 |
| C | 1.00 | 1.10 | 1.20 |
| D | 0.30 | 0.40 | 0.50 |
| E | 0.25 | 0.40 | 0.55 |
| G | | 1.90 | |
| H | 0.00 | - | 0.10 |
| J | 0.047 | 0.127 | 0.207 |
| K | 2.60 | 2.80 | 3.00 |
| All Dimensions in mm | | | |

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